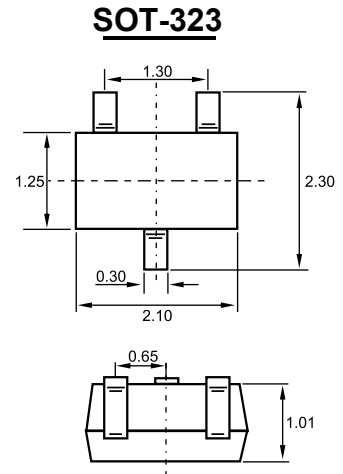
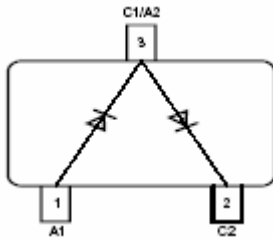


Features

- ◇ For high-speed switching applications
- ◇ Connected in series



Dimensions in inches and (millimeters)

MARKING: KJG

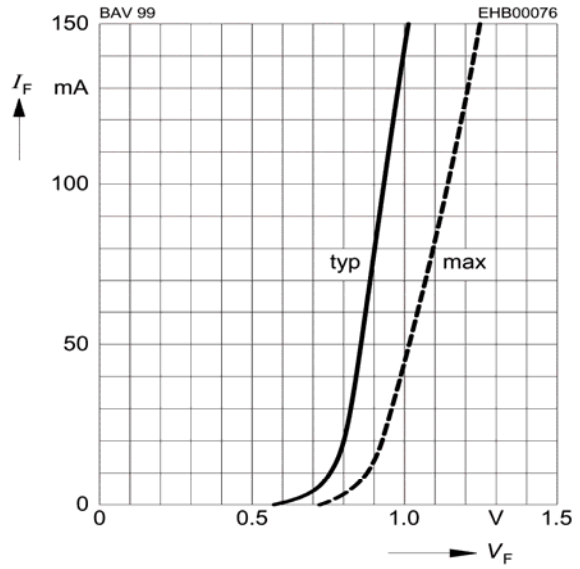
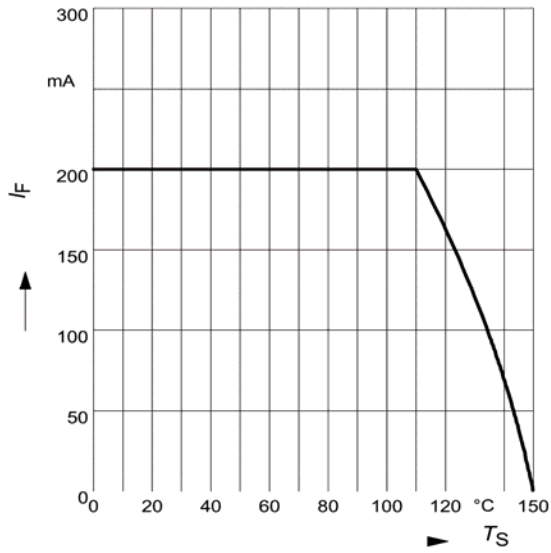
Maximum Ratings @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Limits	Unit
Reverse voltage	V_R	75	V
Forward current	I_o	150	mA
Forward power dissipation	P_D	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65~150	$^\circ\text{C}$

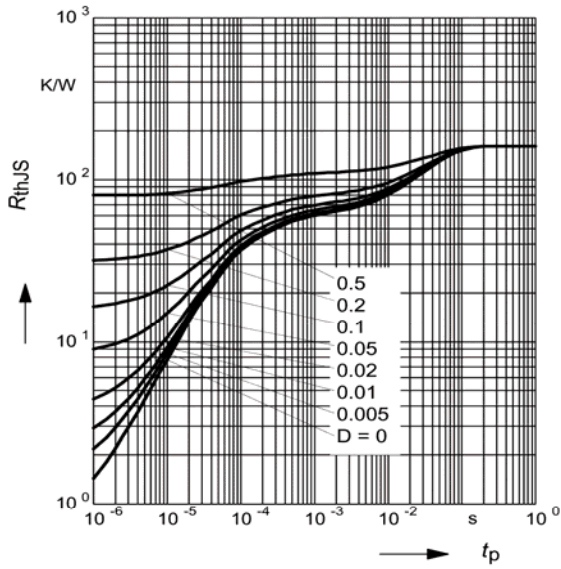
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu\text{A}$	75		V
Reverse voltage leakage current	I_R	$V_R=75\text{V}$ $V_R=20\text{V}$		2.5 25	μA nA
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0\text{V}$ $f=1\text{MHz}$		2	pF
Revers recovery time	t_{rr}	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1 \times I_R$ $R_L=100\Omega$		4	nS

Typical Characteristics

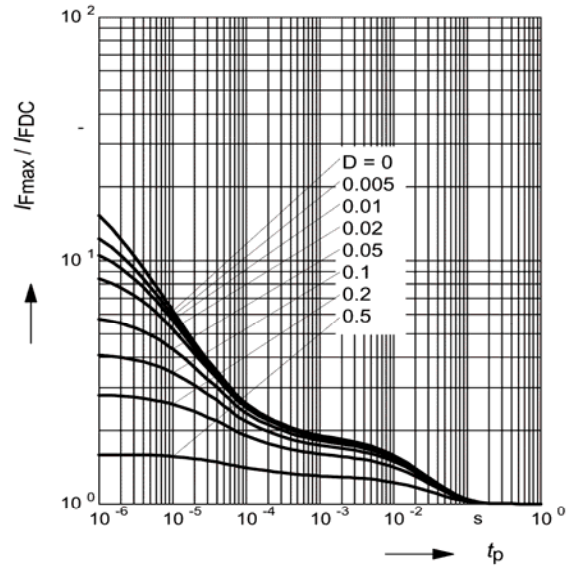


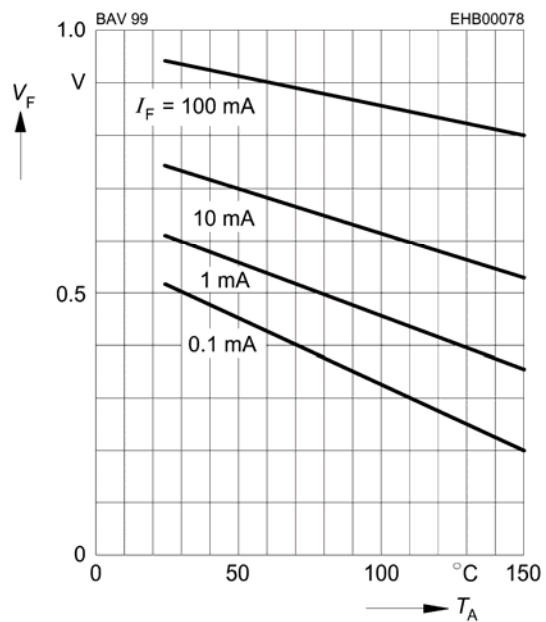
Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$$I_{Fmax} / I_{FDC} = f(t_p)$$



Forward voltage $V_F = f(T_A)$

Reverse current $I_R = f(T_A)$
